MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PLED

BA892WT-MS

Product specification





High Voltage Switching Diode

Applications

for band switching in VHF television tuners and surface mount band switching circuits

Reference News

| SOD-523 | PIN Configuration | Marking |
|---------|-------------------|---------|
| | 1 — 2 | u |

PINNING

| PIN | DESCRIPTION | |
|-----|-------------|--|
| 1 | Cathode | |
| 2 | Anode | |

Absolute Maximum Ratings (T_a = 25℃)

| Parameter | Symbol | Value | Unit |
|-----------------------------|------------------|---------------|------|
| Reverse Voltage | V _R | 35 | V |
| Forward Current | l _F | 100 | mA |
| Junction Temperature | TJ | 150 | °C |
| Operating Temperature Range | T _{op} | - 55 to + 125 | °C |
| Storage Temperature Range | T _{stg} | - 55 to + 150 | °C |

Characteristics at $T_a = 25^{\circ}C$

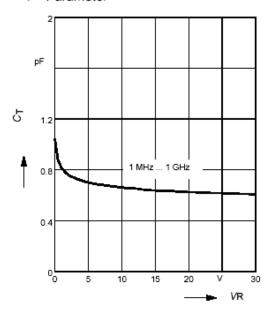
| Parameter | Symbol | Min. | Тур. | Max. | Unit |
|---|----------------|------------------|-------------|-----------------|------|
| Reverse Current at V _R = 20 V | l _R | - | - | 20 | nA |
| Forward Voltage at I _F = 100 mA | V _F | - | - | 1 | V |
| Diode Capacitance at $V_R = 1 \text{ V}$, $f = 1 \text{ MHz}$ at $V_R = 3 \text{ V}$, $f = 1 \text{ MHz}$ at $V_R = 0 \text{ V}$, $f = 100 \text{ MHz}$ | Ст | 0.65 0.6 - | - - 1 | 1.4 1.1 - | pF |
| Forward Resistance at $I_F = 3$ mA, $f = 100$ MHz at $I_F = 10$ mA, $f = 100$ MHz | r _f | - | - | 0.7 0.5 | Ω |
| Series Inductance | Ls | - | 0.6 | - | nΗ |



High Voltage Switching Diode

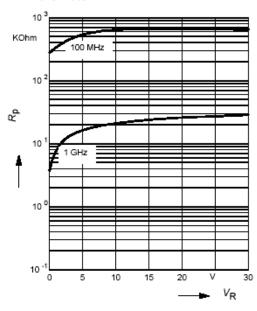
Diode capacitance $C_T = f(V_R)$

f = Parameter



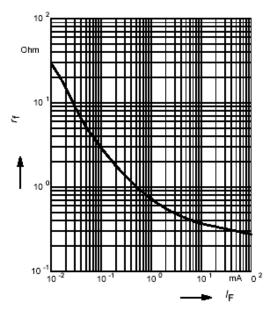
Reverse parallel resistance $R_P = f(V_R)$

f = Parameter



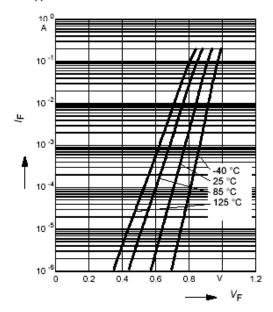
Forward resistance $r_f = f(I_F)$

f = 100MHz



Forward current $I_F = f(V_F)$

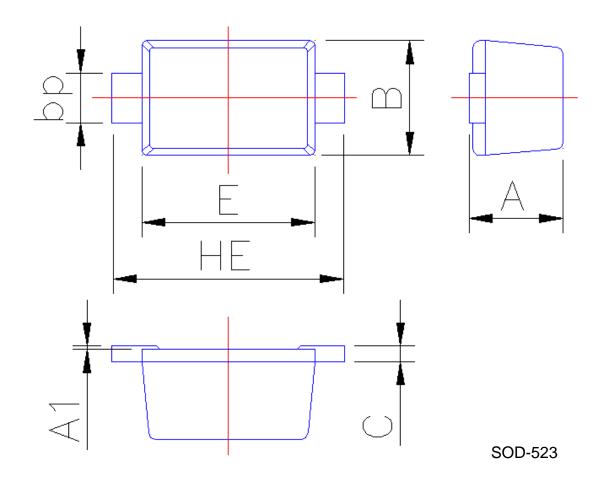
 T_A = Parameter





High Voltage Switching Diode

PACKAGE MECHANICAL DATA



| Symbol | Dimension in Millimeters | | |
|--------|--------------------------|------|--|
| | Min | Max | |
| Α | 0.60 | 0.75 | |
| A1 | 0 | 0.05 | |
| В | 0.75 | 0.85 | |
| bp | 0.25 | 0.40 | |
| С | 0.09 | 0.15 | |
| E | 1.15 | 1.25 | |
| HE | 1.50 | 1.70 | |

REELSPECIFICATION

| P/N | PKG | QTY |
|------------|---------|------|
| BA892WT-MS | SOD-523 | 3000 |



BA892WT-MS

High Voltage Switching Diode

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